



PSMC-03-287/51

March 19, 2004

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

HIGH TEMPERATURE HYDROGEN ANNEALING OF A GATE INSULATOR LAYER TO INCREASE ETCHING SELECTIVITY BETWEEN CONDUCTIVE GATE STRUCTURE AND GATE INSULATOR LAYER

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on March 25, 2004.

Stephen B. Ackerman, Reg. # 37761

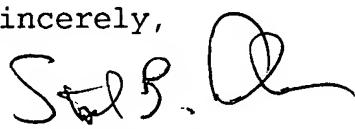
Signature/Date

SPLS. 3/25/04

U.S. Patent 6,335,278 to Miyazaki, "Method of Hydrogen Anneal to a Semiconductor Substrate," discloses a method of hydrogen annealing a semiconductor substrate for forming a semiconductor device such as a semiconductor integrated circuit in order to improve device performance and reliability.

U.S. Patent 6,569,741 to Houston et al., "Hydrogen Anneal before Gate Oxidation," discloses a process for preparing a silicon surface for gate dielectric formation.

Sincerely,



Stephen B. Ackerman,
Reg. No. 37761

~~STOP~~ INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

MAR 2 9 200

(Use several sheets if necessary)

Doctor Number (Optional)

Highway Number

TSmc-03-287/51

10/758,317

卷之三

Vincent S. Chang et al.

Elton Dots

01/15/04

Draw to 1000

MAR 2 9 200

(Use several sheets if necessary)

U. S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portion or Pages, Etc.)

БИБЛИОГРАФИЯ

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.